

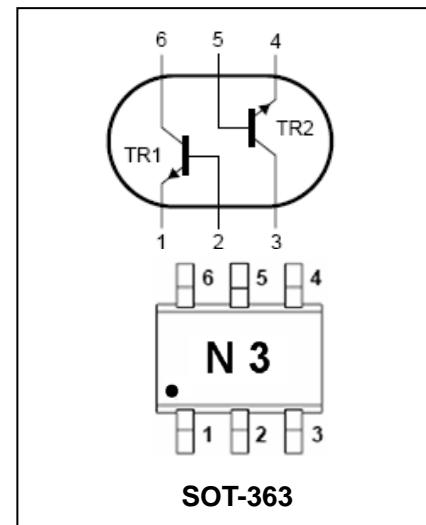
## NPN General Purpose Double Transistor

### FEATURES

- High current(500mA).
- 200mW total power dissipation.
- Replaces two SOT-363 packaged transistors.  
On same PCB area.

### APPLICATIONS

- General purpose switching and amplification.
- Pulse-pull amplifiers.
- Multi-phase stepper motor drivers.
- AEC-Q101 qualified (Automotive grade with suffix "Q".)



### ORDERING INFORMATION

Type No.	Marking	Package Code
BC817DS	N3	SOT-363

### MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	50	V
$V_{CEO}$	Collector-Emitter Voltage	45	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	500	mA
$I_{CM}$	Peak Collector Current	1	A
$I_{BM}$	Peak Base Current	200	mA
$P_{tot}$	Total Power Dissipation	200	mW
$T_{amb}$	Operating Ambient Temperature	-65 to +150	°C
$T_j, T_{stg}$	Junction and Storage Temperature	-65 to +150	°C

ELECTRICAL CHARACTERISTICS @  $T_a=25^\circ\text{C}$  unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	$I_c=10\mu\text{A} I_E=0$	50	-	-	V
Collector-emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	$I_C=10\text{mA} I_B=0$	45	-	-	V
Emitter-base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	$I_E=10\mu\text{A} I_c=0$	5	-	-	V
Collector-base cut-off current	$I_{\text{CBO}}$	$V_{\text{CB}}=20\text{V} I_E=0$ $V_{\text{CB}}=20\text{V} I_E=0 T_j=150^\circ\text{C}$	-	-	100 5	nA $\mu\text{A}$
Emitter-base cut-off current	$I_{\text{EBO}}$	$V_{\text{EB}}=5\text{V} I_c=0$		-	100	nA
DC current gain	$h_{\text{FE}}$	$V_{\text{CE}}=1\text{V} I_c=100\text{mA}$ $V_{\text{CE}}=1\text{V} I_c=500\text{mA}$	160 40	-	400	
Collector-emitter saturation voltage	$V_{\text{CE}(\text{sat})}$	$I_c=500\text{mA} I_B=50\text{mA}$	-	-	0.7	V
Base-emitter on voltage	$V_{\text{BE}}$	$I_c=500\text{mA} V_{\text{CE}}=1.0\text{V}$	-	-	1.2	V
Transition frequency	$f_T$	$V_{\text{CB}}=5.0\text{V}, I_c=10\text{mA}, f=100\text{MHz}$	100	-	-	MHz
Transition capacitance	$C_c$	$V_{\text{CB}}=10\text{V}, f=1.0\text{MHz}$	-	5	-	pF

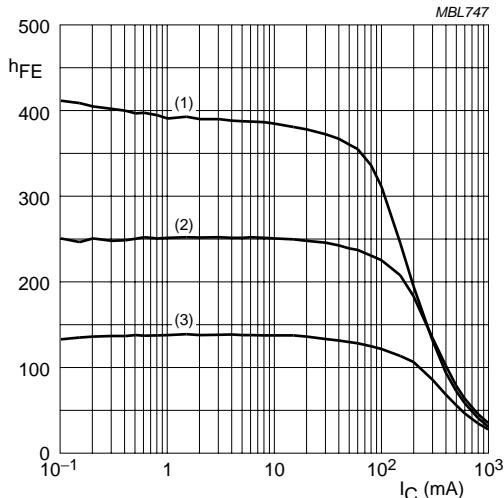
TYPICAL CHARACTERISTICS @  $T_a=25^\circ\text{C}$  unless otherwise specified

Fig.2 DC current gain as a function of collector current; typical values.

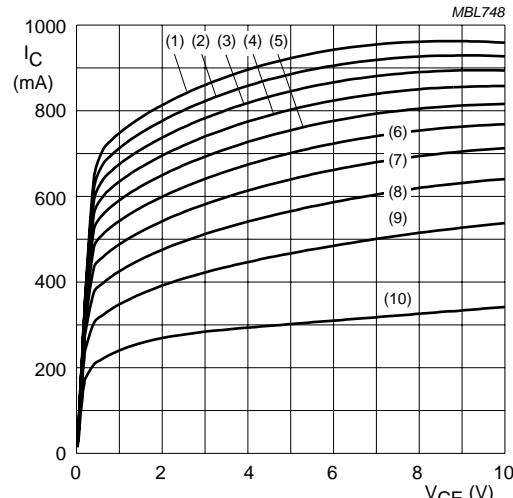


Fig.3 Collector current as a function of collector-emitter voltage; typical values.

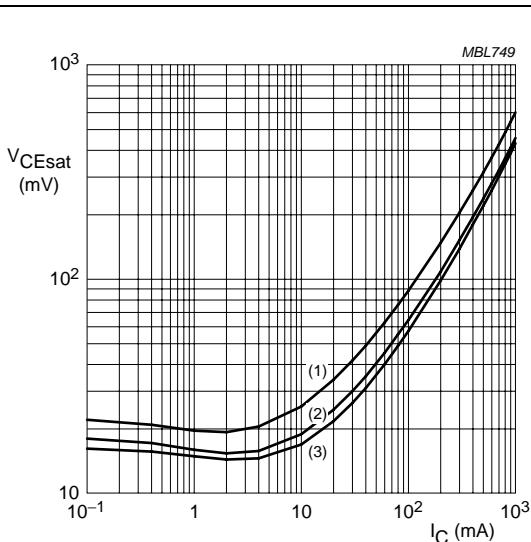


Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.

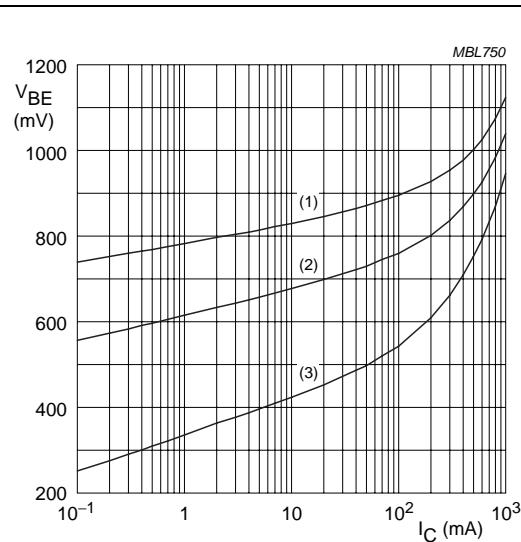
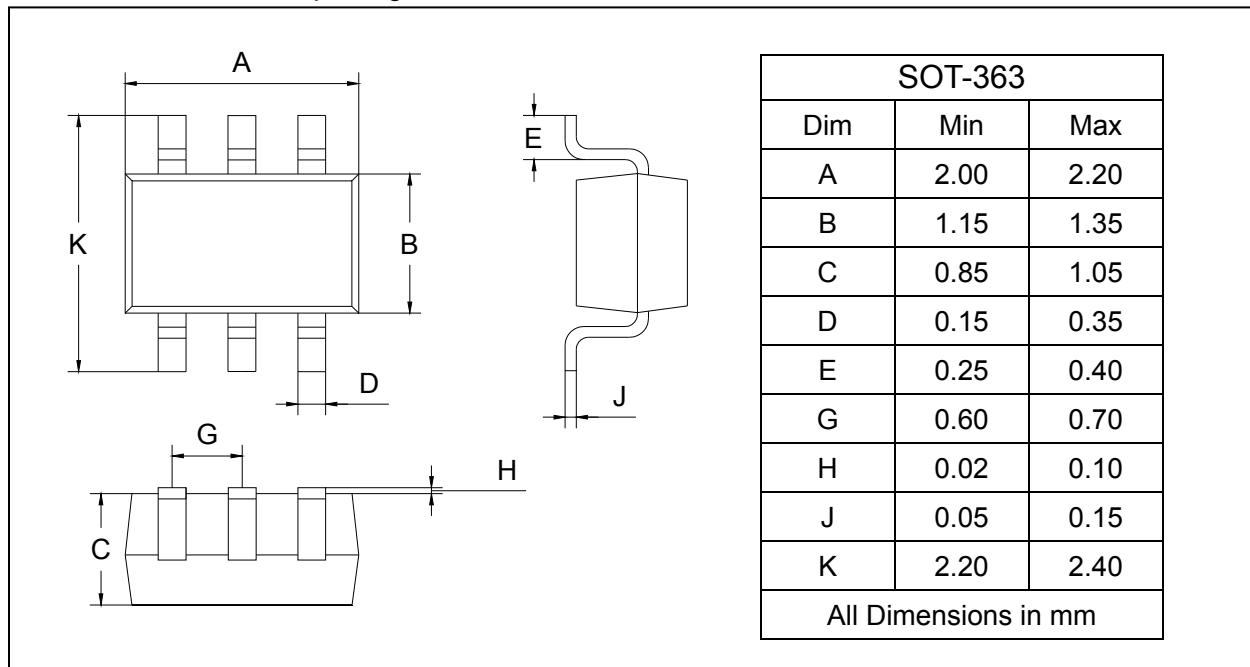


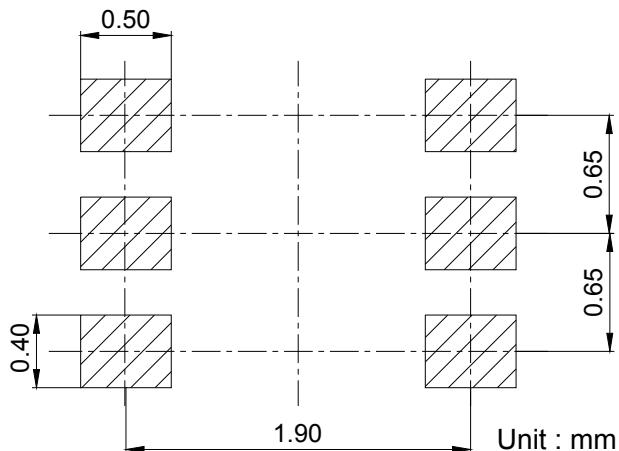
Fig.5 Base-emitter voltage as a function of collector current; typical values.

## PACKAGE OUTLINE

Plastic surface mounted package



## SOLDERING FOOTPRINT



## PACKAGE INFORMATION

Device	Package	Shipping
BC817DS	SOT-363	3000/Tape&Reel